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METHOD OF FABRICATING STACKED STAGGERED ELECTRODE FOIL CAPACITOR STRUCTURES IN SEMICONDUCTOR DEVICES FOR SINGLE AND MULTI-VOLTAGE DOMAIN APPLICATIONS

Abstract

A stacked staggered electrode capacitor in semiconductor devices and methods for fabrication. There are capacitor elements each with a cathode vertically disposed relative to an anode, an anode conductive plating on the anode and a cathode conductive plating on the anode. The anode conductive plating is in a laterally offset relationship to the cathode conductive plating. The plurality of capacitor elements are stacked onto another. One or more build-up layers are interposed between the capacitor elements. One or more anode connecting electrode segments are on a first side of the plurality of capacitor elements, and a cathode connecting electrode on an opposed second side of the plurality of capacitor elements is connected to the cathode conductive plating of each of the plurality of capacitor elements.

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Background/Summary

CROSS-REFERENCE TO RELATED APPLICATIONS [0001] This application is a divisional of U.S. patent application Ser. No. 18/444,455 filed Feb. 16, 2024 and entitled "STACKED STAGGERED ELECTRODE FOIL CAPACITOR STRUCTURES IN SEMICONDUCTOR DEVICES FOR SINGLE AND MULTI-VOLTAGE DOMAIN APPLICATIONS AND METHOD OF FABRICATION," the entire contents of which is expressly incorporated herein by reference.

STATEMENT RE: FEDERALLY SPONSORED RESEARCH/DEVELOPMENT [0002] Not Applicable

BACKGROUND

1. Technical Field

[0003] The present disclosure relates generally to passive electronic devices. More specifically, the present disclosure relates to capacitors in semiconductor devices with stacked staggered-electrode foil structures for single and multi-voltage domain applications, and methods of fabricating the same.

2. Related Art

[0004] Capacitors are an important part of many integrated and embedded circuits and are commonly used as energy storage structures, as primary components in filters and other signal conditioning applications, and as specific components of other types of complex integrated circuits. Capacitors are commonly arranged as a pair of opposing thin electrodes separated by a dielectric, with electrical energy being stored as a consequence of equal and opposite charges on the opposing electrodes. Higher capacitance values may be achieved by a greater surface area of the electrode. [0005] A wide variety of configurations of capacitors as well as packaging modalities are known in the art. In one basic configuration, the electrode and dielectric may be rolled into a tight cylindrical structure to optimize the surface area per unit volume. Another configuration may utilize deep trenches in silicon to benefit from more surface area, or as layers of dielectric and metal stacked and connected to each other. Efforts to maximize capacitance and minimize equivalent series resistance (ESR) of capacitors have led to the development of double-sided capacitors such as those described in co-owned U.S. Pat. App. Pub. No. 2023/006788, entitled "Planar High-Density Aluminum Capacitors for Stacking and Embedding," the entirety of the disclosure of which is incorporated by reference herein. A double-sided capacitor in accordance with the teachings of the disclosure may define a second electrode, e.g., a cathode, of a conductive polymer, metal, or ceramic that is disposed on both sides of a first electrode, e.g., an anode of aluminum that has been etched or otherwise modified to have a high surface area. An oxide layer may be formed between the first and second electrodes to serve as the dielectric.

[0006] One common structure for stacking solid polymer aluminum foil capacitive elements includes a cathode structure that is wrapped around an inner aluminum core anode, with a portion of the aluminum core anode being left untreated or uncoated and extending out from the cathodewrapped inner aluminum core. This structure requires the use of conductive pastes as well as

aluminum welding techniques to join and stack the anode and cathode elements before encapsulation. The reduction of resistance in the inter-element and electrode-to-terminal connections is therefore limited. Such conventional structures are limited in electrode area efficiency and volumetric capacitive density, particularly in advanced substrate core embedding applications with thinner form factors. These conventional structures are also limited to the fabrication of single discrete capacitive elements and are not suitable for integrated passive devices nor can multiple voltage domains be serviced with the single device.

[0007] Accordingly, there is a need in the art for stacked staggered-electrode structures based on solid conductive polymer foil capacitive elements. There is also a need for a higher effective electrode area and increased volumetric capacitive density. Such structures should also be suitable for integrated passive devices that can be embedded into advanced packaging substrates having higher power efficiency architectures that are needed for high power devices.

BRIEF SUMMARY

[0008] A stacked staggered electrode capacitors and methods for fabricating the same are disclosed. Solid-conductive polymer foil-based capacitive elements are utilized, resulting in higher effective electrode area and increased volumetric capacitive density. Co-joined capacitive elements may have common cathodes and discrete anodes suitable for implementation in integrated passive devices serving multiple independent voltage domains. Copper plating in electrode to terminal connections reduces equivalent series resistance, thus increasing power efficiency and reducing thermal load. With top and bottom copper plated terminals, the integrated passive devices may be embedded into advanced packaging substrates supporting high power efficiency architectures needed for high power devices.

[0009] According to one embodiment of the present disclosure, there may be a stacked staggered electrode capacitor. The capacitor may have an anode that is defined by an anode first end and an opposed anode second end. The capacitor may also have a cathode that is disposed vertically relative to the anode and defined by a cathode first end substantially coterminous with the anode second end. The anode may also be defined by an opposed anode second end that is substantially coterminous with the anode first end. The capacitor may include a first conductive plating on the anode, which extends from beyond the anode first end toward the anode second end. Furthermore, the capacitor may have a second conductive plating on the cathode. The second conductive plating may extend from beyond the cathode second end toward the cathode first end. The second conductive plating may be in a staggered relationship relative to the first conductive plating. [0010] Another embodiment of the present disclosure may be a stacked staggered electrode capacitor. The capacitor may include a plurality of capacitor elements each with a cathode disposed vertically relative to an anode. The capacitor element may also include an anode conductive plating on the anode and a cathode conductive plating on the anode. The anode conductive plating may be in a laterally offset relationship to the cathode conductive plating. The plurality of capacitor elements be stacked onto another. The capacitor may also include one or more build-up layers, each of which may be interposed between one of the plurality of capacitor elements and a vertically adjacent one of the plurality of capacitor elements. The capacitor may further include one or more anode connecting electrode segments on a first side of the plurality of capacitor elements, as well as a cathode connecting electrode on an opposed second side of the plurality of capacitor elements that is connected to the cathode conductive plating of each of the plurality of capacitor elements. [0011] The embodiments of the present disclosure also include a method for fabricating a stacked staggered electrode capacitor. The method may include coating a conductive polymer cathode layer on to a planar anode sheet to form one or more capacitor core assemblies. Each of the capacitor core assemblies may be defined by an assembly top surface corresponding to a cathode and an assembly bottom surface corresponding to an anode. There may be a step of forming one or more vertical insulator channels that are spaced apart along the one of the capacitor core assemblies. The method may further include filling the vertical insulator channels with an insulator epoxy material.

The method may also involve seed metallizing the assembly top surface and the assembly bottom surface to form a seeded cathode metal layer and a seeded anode metal layer. There may additionally be a step of plating the seeded cathode metal layer and the seeded anode metal layer to form a cathode electrode plating and an anode electrode plating. The method may include etching the cathode electrode plating and the anode electrode plating to respectively define a top opening and a bottom opening to the insulator epoxy material. The cathode electrode plating may be staggered relative to the anode electrode plating with the top opening being laterally offset from the bottom opening.

[0012] The method for fabricating the capacitor may also include a step of laminating a plurality of the capacitor core assemblies. Build-up layers may separate one of the capacitor core assemblies from another. Together, the capacitor core assemblies and the build-up layers may form a capacitor stack. The method may also include routing one or more slots through the capacitor stack at least partially coextensively with the top and bottom openings defined by the cathode electrode plating and the anode electrode plating of respective ones of the capacitor core assemblies. There may also be a step of metal plating the one or more slots. A cathode connecting electrode may be defined along a first side of one of the slots and electrically connected to the cathode electrode plating of at least one of the capacitor core assemblies. An anode connecting electrode may be defined along a second side of one of the slots and electrically connected to the anode electrode plating of at least one of the capacitor core assemblies.

Description

BRIEF DESCRIPTION OF THE DRAWINGS

[0013] These and other features and advantages of the various embodiments disclosed herein will be better understood with respect to the following description and drawings, in which like numbers refer to like parts throughout, and in which:

[0014] FIG. **1** is a cross-sectional view of an exemplary stacked staggered electrode foil capacitor according to one embodiment of the present disclosure;

[0015] FIG. **2** is a detailed cross-sectional view of a capacitor element or core assembly incorporated into the stacked staggered electrode foil capacitor;

[0016] FIG. **3** is a cross-sectional view of an exemplary stacked staggered electrode foil capacitor according to another embodiment of the present disclosure;

[0017] FIG. **4**A is a flowchart illustrating a first part of a method for fabricating the stacked staggered electrode foil capacitor according to an embodiment of the present disclosure;

[0018] FIG. **4**B is a flowchart illustrating a second part of the method for fabricating the stacked staggered electrode foil capacitor;

[0019] FIGS. **5**A-**5**G are cross-sectional views of a capacitor core assembly at various stages of fabrication;

[0020] FIGS. **6**A-**6**D are cross-sectional views of a stacked staggered electrode capacitor at various stages of fabrication following the stacking of multiple capacitor core assemblies;

[0021] FIG. **7** is a simplified cross-sectional view of another embodiment of the stacked staggered electrode capacitor at a stage of fabrication after connecting terminals have been formed; and [0022] FIG. **8** is a simplified cross-sectional view of the stacked staggered electrode capacitor shown in FIG. **7** after singulation.

DETAILED DESCRIPTION

[0023] The detailed description set forth below in connection with the appended drawings is intended as a description of the several presently contemplated embodiments of stacked staggered electrode foil capacitor structures for single and multiple domain applications and methods of their fabrication. It is not intended to represent the only form in which such embodiments may be

developed or utilized. The description sets forth the functions and features in connection with the illustrated embodiments. It is to be understood, however, that the same or equivalent functions may be accomplished by different embodiments that are also intended to be encompassed within the scope of the present disclosure. It is further understood that the use of relational terms such as first and second, top and bottom, left and right and the like are used solely to distinguish one from another entity without necessarily requiring or implying any actual such order or relationship between such entities.

[0024] Referring now to FIG. **1**, various embodiments of the present disclosure contemplate a stacked staggered electrode foil capacitor **10**, also referred to herein as capacitor **10**, comprised of multiple capacitor elements **12** or capacitor core assemblies. In the illustrated example, there are five (5) capacitor elements stacked on top of each other, including a first capacitor element **12***a* at an uppermost end **14** of the capacitor **10**, a second capacitor element **12***b* below the first capacitor element **12***a*, a third capacitor element **12***c* below the second capacitor element **12***b*, a fourth capacitor element **12***d* below the third capacitor element **12***c*, and a fifth capacitor element **12***e* at the lowermost end **16** of the capacitor **10**. Notwithstanding the embodiment of FIG. **1** showing five capacitor elements **12**, it is to be understood that this is by way of example only and not of limitation. Other embodiments may incorporate additional capacitor elements **12**, or fewer capacitor elements **12**.

[0025] Each of the capacitor elements **12***a***-12***e* are understood to have the same configuration, and so for the purposes of brevity, additional features thereof will be described in the context of the first capacitor element **12***a* shown in further detail in FIG. **2**. It is to be understood that such features are applicable to the remaining capacitor elements **12***b***-12***e* of the stacked staggered electrode foil capacitor **10**. In further detail, the capacitor element **12** includes an anode **18** that has an elongate planar structure with an anode first end **20** and an opposed anode second end **22**. Additionally, the elongated planar structure of the anode **18** is defined by an anode top surface **24** and an anode bottom surface **26**. According to various embodiments, the anode **18** is an electrically conductive metal or metal alloy foil. Preferably, though optionally, the metal foil is aluminum, though any other suitable electrically conductive material may be substituted without departing from the present disclosure.

[0026] The capacitor element 12 further includes a cathode 28, which has an elongate planar structure with a cathode first end **30** and an opposed cathode second end **32**. Although the anode **18** and the cathode **28** are depicted as two physically separate layers, it is to be understood that they are constructed from a single sheet of foil material. The cathode **28** is defined on the upper portion of the foil by the formation of a dielectric on an etched high surface area followed by conformal coating with a conductive polymer. Accordingly, the cathode 28 may be described as being vertically disposed relative to the anode 18 even though the anode 18 and the cathode 28 may be physically contiguous. The elongated planar structure of the cathode 28 has a cathode top surface **34** and a cathode bottom surface **36** that faces and is adjacent to the anode top surface **24**. In other words, a connecting interface between the cathode **28** and the anode **18** is defined by the respective cathode bottom surface **36** and the anode top surface **24**. These cathode bottom surface **36** and the anode top surface **24** depicted with clear boundaries herein solely for the purpose of distinguishing the anode **18** from the cathode, and it is not implied that a fabricated device will exhibit such clear physical boundaries. In this regard, the thickness of the anode **18** and the cathode **28**, or the thickness ratio of the same, are not intended to be limited to that which is shown in the figures. The cathode first end **30** is substantially coterminous with the anode second end **22**, while the cathode second end **32** is substantially coterminous with the anode first end **20**. The cathode **28** is likewise understood to be a conductive material. Preferably, though optionally, this may be a polymer foil. [0027] Generally, however, the selection of material for the anode **18** and the cathode **28** may be varied according to the desired capacitance and dielectric constant values for the particular capacitor element **12** and/or the overall stacked staggered electrode capacitor **10**. Similarly, the

thickness and lengthwise/widthwise dimensional parameters may also be varied according to the particular application and desired characteristics.

[0028] Each capacitor element **12** also has a first conductive plating **38** on the anode **18**. With the orientation of the capacitor **10** shown in FIG. **1**, the anode **18** appears stacked on to the first conductive plating **38**, though as will be described in further detail below, a metal plating is applied to the anode bottom surface **26** following a seed metallization step. Accordingly, underneath the anode **18** is an anode conductive seed layer **40**. As referenced herein, stacking refers generally to the top-to-bottom positional relationship of one component relative to another, such as the anode 18 being disposed above the first conductive plating 38 with the anode conductive seed layer 40 interposed between and is not limited to the physical placing of one component on top of another. Opposite the anode conductive seed layer **40**, the first conductive plating **38** defines a bottom conductive plating surface **42** and extends from beyond the anode first end **20**. More particularly, the first conductive plating **38** defines a first conductive plating first end **44** that is laterally offset from the anode first end 20. The first conductive plating 38 extends across the anode 18 and defines a first conductive plating second end **46** that is substantially coterminous with the anode second end **22** and the cathode first end **30**. In accordance with various embodiments of the present disclosure, the first conductive plating **38** may be copper. It will be appreciated that the copper plating in the electrode-to-terminal connections such as that of the first conductive plating and the anode **18** yields a reduction in the equivalent series resistance of the capacitor **10** overall, which in turn increases power efficiency and reduces thermal load thereon.

[0029] Each capacitor element **12** further incorporates a second conductive plating **48** on the cathode **28**.

[0030] With the orientation of the capacitor **10** shown in FIG. **1**, the second conductive plating **48** appears stacked on to the cathode 28, but again, a metal plating is applied to the cathode top surface **34** following a seed metallizing step with a cathode conductive seed layer **50** being between the cathode **28** and the second conductive plating **48**. Like the first conductive plating **38**, the second conductive plating **48** is copper. Opposite the cathode conductive seed layer **50**, the second conductive plating **48** defines a top conductive plating surface **52** and extends from beyond the cathode first end **30**. The second conductive plating **48** defines a second conductive plating first end **54** that is laterally offset from the cathode first end **30**. The second conductive plating **48** extends across the cathode **28** and defines a second conductive plating second end **56** that is substantially coterminous with the cathode second end **32** as well as the anode first end **20**. [0031] Because the first conductive plating **38** extends from beyond the right side bounds of the anode **18** and the cathode **28**, and the second conductive plating **48** extends from beyond the left side bounds of the anode **18** and the cathode **28**, the first conductive plating **38** is understood to be laterally offset or staggered relative to the second conductive plating **48**. As will be described in further detail below, this permits interconnections of the first conductive plating **38** of one or more of the capacitor elements 12 on the right side, and the interconnections of the second conductive plating **48** of one or more of the capacitor element **12** on the left side. In the embodiments of the present disclosure, there is understood to be a vertical spacing of the first conductive plating **38** (also referred to as the anode terminal because of the connection to the anode 18) relative to the second conductive plating **48** (also referred to as the cathode terminal because of the connection to the cathode **28**). The cathode terminal **48** being staggered or laterally offset to the anode terminal **38** means that each has a central region of overlap in the context of the vertically spaced or offset relationship, while each has extending regions without overlap in opposite directions. For example, the cathode terminal **48** extends to the left beyond the leftmost edge of the anode terminal **38**, while the anode terminal **48** extends to the right beyond the rightmost edge of the cathode terminal **48**. Disposed to the right of the anode **18** and the cathode **28** in the intermediate vertical space bounded by the anode first end **20**/cathode second end **32** and the first conductive plating first end **44** is a first insulator **58**. Similarly, on the opposite side, disposed to the left of the anode **18** and the

cathode **28** in the intermediate vertical space bounded by the anode second end **22**/cathode first end **30** and the second conductive plating first end **54** is a second insulator **60**. Both the first insulator **58** and the second insulator **60** may have a height or thickness that is equal to that of the stacked anode **18** and cathode **28**. The first insulator **58** and the second insulator **60** may be a nonconductive polymer/epoxy material.

[0032] The first conductive plating **38** is structurally contiguous and in electrical communication with an anode connecting electrode **62** that extends in a normal or perpendicular relationship to the anode **18** and the cathode **28**. The first conductive plating first end **44** is thus proximal to the anode connecting electrode **62**. With the first insulator **58** being interposed between the inner wall of the anode connecting electrode **62** and the anode first end **20**/cathode second end **32**, the cathode **28** is isolated from the anode connecting electrode **62**. As indicated above, the anode **18** is in electrical communication with the first conductive plating **38**, which in turn is in electrical communication with the anode connecting electrode **62**.

[0033] Similarly, the second conductive plating **48** is structurally contiguous and in electrical communication with a cathode connecting electrode **64** that extends in a normal or perpendicular relationship to the anode **18** and the cathode **28**. The second conductive plating first end **54** is proximal to the cathode connecting electrode **64**. With the second insulator **60** being interposed between the inner wall of the cathode connecting electrode **64** and the cathode first end **30**/anode second end **22**, the anode **18** is isolated from the cathode connecting electrode **64**. The cathode **28** is in electrical communication with the second conductive plating **48**, which in turn is in electrical communication with the cathode connecting electrode **64**.

[0034] Referring back to FIG. **1**, the capacitor **10** is comprised of a plurality of capacitor elements **12** that are stacked onto another. Separating each of the capacitor elements **12** are build-up layers **66**. In the exemplary embodiment of the capacitor **10** with five capacitor elements, there is a first intermediate build-up layer **66***a* between the first capacitor element **12***a* and the second capacitor element **12***b*, a second intermediate build-up layer **66***b* between the second capacitor element **12***b* and the third capacitor element **12***c*, a third intermediate build-up layer **66***c* between the third capacitor element **12***c* and the fourth capacitor element **12***d*, and a fourth intermediate build-up layer **66***d* between the fourth capacitor element **12***d* and the fifth capacitor element **12***e*. Each of the intermediate build-up layers **66***a***-66***d* may have a generally planar configuration extending between the inner walls of the anode connecting electrode 62 and the cathode connecting electrode 64, and adjacent to the bottom conductive plating surface 42 of one capacitor element 12 and the top conductive plating surface **52** of the next one immediately underneath. Above the first capacitor element **12***a* is a top build-up layer **68**, and below the fifth capacitor element **12***e* is a bottom buildup layer **70**. All of the aforementioned build-up layers may be an electrically insulating polymer sheet or film, which may optionally be Ajinomoto® Buildup Film. Generally, the build-up layer may be modified epoxy, glass-reinforced pre-preg materials commonly utilized in printed circuit board constructions.

[0035] According to one embodiment, the anode connecting electrode **62** of each of the capacitor elements **12***a***-12***e* may be connected to define a contiguous anode electrode **72** that extends vertically along the right side of the overall structure of the capacitor **10**. Similarly, the cathode connecting electrode **64** of each of the capacitor elements **12***a***-12***e* may be connected to define a contiguous cathode electrode **74** that extends along the left side of the overall structure of the capacitor **10**. The anode connecting electrode **62** and the cathode connecting electrode **64** may be considered as being defined by multiple segments when considered in the context of single capacitor element in the overall stack, but according to various embodiments, the segments may be combined into a single unitary structure. With the first conductive plating **38** on each of the anodes **18** extending to the anode electrode **72** but not the second conductive plating **48**, the cathodes **28** remain isolated from the anodes **18**/anode electrode **72**. Likewise, with the second conductive plating **48** on each of the cathodes **28** extending to the cathode electrode **74** but not the first

conductive plating **38**, the anodes **18** remain isolated from the cathodes **28**/cathode electrode **74**. [0036] The top build-up layer **68** defines a top surface **76**, along which there may extend a top anode terminal segment **78** that is structurally contiguous with the anode electrode **72**, as well as a top cathode terminal segment **80** that that is structurally contiguous with the cathode electrode **74**. Neither are understood to extend the entire width of the capacitor **10**, and so there may be a top opening **82** defined by the inner extent of the top anode terminal segment **78** and the top cathode terminal segment **80**.

[0037] Similar features are contemplated for the bottom portion of the capacitor **10**, with a bottom surface **86** being defined by the bottom build-up layer **70**. There may be a bottom anode terminal segment **88** that is structurally contiguous with the anode electrode **72**, and a bottom cathode terminal segment **90** that is structurally contiguous with the cathode electrode **74**. Like the top anode and cathode terminal segments **78**, **80**, the bottom anode and cathode terminal segments **88**, **90** may not extend the entire width of the capacitor **10**. These terminal segments may together define a bottom opening **92**.

[0038] In the foregoing embodiment, the anode **18** and the cathode **28** of each of the capacitor elements 12 have common connections due to the structurally and electrically contiguous anode electrode **72** and the structurally and electrically contiguous cathode electrode **74**. An additional embodiment suitable for servicing multiple independent voltage domains in an integrated passive device (IPD) is also contemplated. As best shown in FIG. 3, though with additional reference to FIG. **2**, a capacitor **11** may be comprised of a first capacitor block **10***a* and a second capacitor block **10***b*. The first capacitor block **10***a* largely corresponds to the capacitor **10** as described above, and includes the capacitor elements **12***a***-12***e*. Each of these capacitor elements **12** are configured with the second conductive plating **48** extending to the cathode electrode **74**, while stopping short of the anode electrode 72. The first conductive plating 38 of each of the capacitor elements 12, on the other hand, extend to the anode electrode 72 while stopping short of the cathode electrode 74. [0039] The second capacitor block **10***b*, on the other hand, is horizontally mirrored with respect to the staggering of the cathode and anode terminals. In further detail, the second capacitor block **10***b* is comprised of capacitor elements 12', including a first capacitor element 12'a, a second capacitor element **12**′*b*, a third capacitor element **12**′*c*, a fourth capacitor element **12**′*d*, and a fourth capacitor element 12'e. Each of the capacitor elements 12' are understood to include a first conductive plating 38' (connected to the cathode 18') that extends to an anode electrode 72' but does not extend to a cathode electrode **74**′, as well as a second conductive plating **48**′ (connected to the cathode **28**′) that extends to the cathode electrode 74' but does not extend to the anode electrode 72'. [0040] The anode electrode **72** of the first capacitor block **10***a* is located on a right side **300** of the capacitor **11**, and the cathode electrode **74** of the first capacitor block **10***a* is located in a rightward central region **302**. The cathode electrode **74**′ of the second capacitor block **10***b* is located in a leftward central region **304**, while the anode electrode **72**′ of the second capacitor block **10***b* is located on a left side **306** of the capacitor **11**. Thus, the cathode electrode **74** of the first capacitor block 10a is adjacent to the cathode electrode 74' of the second capacitor block 10b, and are electrically contiguous with each other. In other words, the first capacitor block **10***a* shares a common cathode with the second capacitor block **10***b*, while the anode electrode **72** of the first capacitor block **10***a* remains isolated from the anode electrode **72**′ of the second capacitor block **10***b*. In this configuration, the first capacitor block **10***a* and the second capacitor block **10***b* may service independent voltage domains in a single arrayed integrated passive device. [0041] There may also be a gap **75** defined between the cathode electrode **74** of the first capacitor block 10a and the cathode electrode 74' of the second capacitor block 10b, with the structural and electrical connections between the two being established over a top terminal bridge **310** and a bottom terminal bridge **312**. The top terminal bridge **310** may connect the top cathode terminal segment **78** of the first capacitor block **10***a* and a top cathode terminal segment **78**′ of the second capacitor block **10***b*. The bottom terminal bridge **312** may connect the bottom cathode terminal

segment **88** of the first capacitor block $\mathbf{10}a$ and a bottom cathode terminal segment $\mathbf{88}'$ of the second capacitor block $\mathbf{10}b$.

[0042] The embodiments of the stacked staggered electrode foil capacitor 10 may be fabricated in accordance with various methods, with a portion of one such method being shown in the flowchart of FIG. 4A. The cross-sectional views of FIGS. 5A-5G illustrate the capacitive element 12 in various stages of completion as corresponding to the specific steps of the method. The method begins with a step 100-1 of coating a conductive polymer cathode layer 128 on to a planar anode sheet 118 to form a capacitor core assembly 112. Upon completion, the conductive polymer cathode layer 128 becomes the cathode 28, the planar anode sheet 118 becomes the anode 18, and the capacitor core assembly 112, with the addition of further components, becomes the capacitor element 12. The details of the anode 18, the cathode 28, and the capacitor element 12 generally, including its structural and material parameters have been discussed above. Accordingly, such details will be omitted for the sake of brevity. The capacitor core assembly 112 defines an assembly top surface 200 that corresponds to the cathode 28 and an assembly bottom surface 202 that corresponds to the anode 18. FIG. 5A illustrates the capacitor core assembly 112 after completion of the step 100-1. As best shown in FIG. 5B, the capacitor core assembly 112 may be mounted to a frame 204 to enable the next step in the fabrication process.

[0043] The method continues with a step **100-2** of forming one or more vertical insulator channels **206**. As depicted in FIG. **5**C, there may be a first vertical insulator channel **206** and a second vertical insulator channel **206**. It is to be understood that the cross-sectional views of FIGS. **5**A-**5**G are excerpts of a section of the capacitor core assembly **112**. In practice, the constituent sheets of material may extend to arbitrary widths, thicknesses, and other dimensions, so there may be additional vertical insulator channels **206** spaced across the capacitor core assembly **112**. Those having ordinary skill in the art will appreciate any restrictions imposed by existing or future tooling and processes. The vertical insulator channels **206** extend through the planar anode sheet **118** and the conductive polymer cathode layer **128**, but not the frame **204**.

[0044] Next, in a step **100-3**, the method involves filling the vertical insulator channels **206** with an insulator epoxy material. As shown in FIG. **5**D, with there being the first vertical insulator channel **206***a* and the second vertical insulator channel **206***b*, following completion of the step **100-3**, there is a corresponding insulator epoxy section **208***a* and an insulator epoxy section **208***b*. The height of the insulator epoxy sections **208** is understood to be the same as the planar anode sheet **118** and the conductive polymer cathode layer **128** combined.

[0045] Following the fabrication of the insulator epoxy sections **208**, the method continues with a seed metallization step **100-4** that prepares the planar anode sheet **118** and the conductive polymer cathode layer **128** to accept the copper or other metal plating. FIG. **5**E depicts the cathode conductive seed layer **50** that is formed on the assembly top surface **200** corresponding to the conductive polymer cathode layer **128** and the anode conductive seed layer **40** that is formed on the assembly bottom surface **202** corresponding to the planar anode sheet **118**. The anode conductive seed layer **40** may be referred to as a seeded anode metal layer and the cathode conductive seed layer **50** may be referred to as a seeded cathode metal layer.

[0046] Upon completing the seed metallization step, the method proceeds to a metal plating step **100-5** that forms an anode electrode plating **210** on the anode conductive seed layer **40** and a cathode electrode plating **212** on the cathode conductive seed layer **50**. The anode electrode plating **210** is understood to correspond to the first conductive plating **38** discussed in the context of the structural features of the capacitor elements **12** discussed above. Similarly, the cathode electrode plating **212** corresponds to the second conductive plating **48**. Broad boundaries between different segments of the conductive plating may be established around the insulator epoxy sections **208**, with plating gaps **214** being present in the resulting capacitor core assembly **112**.

[0047] The method continues with a step **100-6** of etching the metal plating, e.g., the anode electrode plating **210** and the cathode electrode plating **212** to further define the staggered

relationship. As a result, a further bottom opening **216** may be defined along the bottom face of the capacitor core assembly **112**, as well as a top opening **218** that is defined along the top face. The opening **216** extends through the anode conductive seed layer **40** to the insulator epoxy section **208**, while the opening **218** extends through the cathode conductive seed layer **50** likewise to the insulator epoxy section **208**. The bottom and top openings **216**, **218** are laterally offset from each other, such that the anode electrode plating **210** is staggered relative to the cathode electrode plating **212**.

[0048] The foregoing steps are directed to fabricating one capacitor core assembly **112**. The method for fabricating the staggered electrode stacked capacitor **10** further includes assembling multiple capacitor core assemblies **112**, the steps for which are shown in the flowchart of FIG. **4B**. The step **100** of fabricating the capacitor core assembly **112** consolidates the steps **100-1** to **100-6** described above, and then proceeds to a lamination step **102**.

[0049] In the illustrated example, five capacitor core assemblies **112** are stacked atop each other, including a first capacitor core assembly **112***a*, a second capacitor core assembly **112***b*, a third capacitor core assembly **112***c*, a fourth capacitor core assembly **112***d*, and a fifth capacitor core assembly 112e. Interposed between each capacitor core assembly 112 are build-up layers 66, 68, **70**. Again, atop the first capacitor core assembly **112***a* is the top build-up layer **68**, and under the fifth capacitor core assembly **112***e* is the bottom build-up layer **70**. Between the first capacitor core assembly **112***a* and the second capacitor core assembly **112***b* is the first intermediate build-up layer **66***a*, between the second capacitor core assembly **112***b* and the third capacitor core assembly **112***c* is the second intermediate build-up layer **66***b*, between the third capacitor core assembly **112***c* and the fourth capacitor core assembly **112***d* is the third intermediate build-up layer **66***c*, and between the fourth capacitor core assembly **112***d* and the fifth capacitor core assembly **112***e* is the fourth intermediate build-up layer **66***d*. The lamination process may begin from the bottom build-up layer **70** and stacking the fifth capacitor core assembly **112***e*, then the fourth intermediate build-up layer **66***d*, and so forth. Other embodiments may involve the reverse, beginning with the top build-up layer **68** and fixing the first capacitor core assembly **112***a* onto the top build-up layer **66**, and so on. Still other embodiments may involve alternatively stacking on top of and below a given one of the capacitor core assemblies 112 and build-up layers 66, 68, and 70. At the conclusion of the lamination step 102, a capacitor stack 220 results.

[0050] Referring back to the flowchart of FIG. 4B as well as the cross-sectional view of FIG. 6B, the method continues with a step **104** of routing slots **222** through the capacitor stack **220**. Preferably, though optionally, the slot **222** extends through the center of the insulator epoxy section **208**, with an equal length of the anode electrode plating **210** on one side of the slot **222** and the cathode electrode plating 212 on the other side of the slot 222 remaining underneath and below, respectively, the insulator epoxy section **208**. In general, the slots **222** are at least partially coextensive with the bottom opening **216** and the top opening **218** of the capacitor core assemblies 112. The slots 222 may also be vias, and accordingly may have any cross-sectional profile. [0051] After the slots **222** are routed in accordance with step **104**, the method continues with a step **106** of metal plating the same. As best shown in FIG. **6**C, this plating process forms the anode connecting electrode **62**, which connects to the first conductive plating **38** of each of the capacitor core assemblies **112**, as they extend beyond the limits of the second conductive plating **48**. The plating process also forms the cathode connecting electrode **64** that connects to the second conductive plating **48** of each of the capacitor core assemblies **112**. The slot **222** is understood to be bounded by a left wall that corresponds to the anode connecting electrode **62**, and a right wall that corresponds to the cathode connecting electrode **64**. [**0055**] The method concludes with a step **108** of singulating the staggered electrode stacked capacitor **10** from the others in the capacitor stack **220**.

[0052] In an alternative embodiment, the fabrication method may yield the capacitor **11** with independent anodes and a shared cathode. The step **100-6** of etching the metal plating discussed

above with reference to FIG. **5**F, **5**G may be modified for a pattern in which the staggering of the anode electrode plating **210** and the cathode electrode plating **212** on one (center) pair of capacitor core assemblies **112** is reoriented so that the cathode terminals **74** are back-to-back in neighboring capacitor blocks **10**. FIG. **7** is a simplified cross sectional view of the capacitor stack **220**, showing the shared cathode terminal **74**, **74**′, the anode terminal **74** of the first capacitor block **10***a* and the anode terminal **74**′ of the second capacitor block **10***b*.

[0053] During the manufacturing process, multiple capacitors **11** are understood to be fabricated on a single capacitor stack **220**. Thus, there may be an anode terminal **72**′ of another adjacent one of the second capacitor blocks **10***b* that is spaced apart from the anode terminal **72**. In the illustrated example, this anode terminal 72'-2 is disposed to the right of the anode terminal 72. Likewise, there may be an anode terminal **72-0** of another adjacent one of the first capacitor blocks **10***b* spaced apart from the anode terminal 72'. Specifically, this anode terminal 72-0 is disposed to the left of the anode terminal **72**′. FIG. **7** also depicts the cathode terminal **74-0** of this other second capacitor block **10***b***-0**, and the cathode terminal **74-2** of the other first capacitor block **10***a***-2**. [0054] The method continues with a step **100-6** of etching the metal plating, e.g., the anode electrode plating **210** and the cathode electrode plating **212** to further define the staggered relationship. As a result, a further bottom opening **216** may be defined along the bottom face of the capacitor core assembly **112**, as well as a top opening **218** that is defined along the top face. The opening **216** extends through the anode conductive seed layer **40** to the insulator epoxy section **208**, while the opening **218** extends through the cathode conductive seed layer **50** likewise to the insulator epoxy section **208**. The bottom and top openings **216**, **218** are laterally offset from each other, such that the anode electrode plating **210** is staggered relative to the cathode electrode plating **212**.

[0055] FIG. **11** illustrates the terminals of the capacitor **11** after singulation, including the shared cathode terminal **74**, **74**′, as well as the independent anodes **72** and **72**′. As described above, the cathode terminal **74** and the anode **72** are a part of the first capacitor block **10***a*, and the cathode terminal **74**′ and the anode **72**′ are a part of the second capacitor block **10***b*.

[0056] The fabricated capacitors **10**, **11** are envisioned to have a high electrode area density, and as a consequence, high electrode efficiency. Along these lines, the capacitors **10**, **11** have high volumetric capacitive density and increased stacked element density, particularly in comparison to earlier foil-based capacitors. As indicated above, the copper electrodes and interconnects yield low equivalent series resistance overall, along with high reliability and low resistance with respect to electrode and terminal connections. The staggered electrode stacked capacitors **10**, **11** are wellsuited for embedding in packaging substrate core structures, particularly integrated passive devices capable of handling multiple voltage domains. It is expressly contemplated that the capacitors 10, 11 in accordance with various embodiments of the present disclosure may be incorporated into high performance compute applications such as in data centers, artificial intelligence/deep learning integrated circuits, graphic processing units, field programmable gate array (FPGA) circuits, analog and radio frequency (RF) power and filter architectures, electric vehicle power architectures, and other electric motor driver applications. The integration of the capacitive elements closer to the serviced load, as would be possible with the devices in accordance with the present disclosure, is envisioned to increase power efficiency, increase system performance, and reduce thermal loading. [0057] The particulars shown herein are by way of example and for purposes of illustrative discussion of the embodiments of the stacked staggered electrode foil capacitor structures and are presented in the cause of providing what is believed to be the most useful and readily understood description of the principles and conceptual aspects. In this regard, no attempt is made to show details with more particularity than is necessary, the description taken with the drawings making apparent to those skilled in the art how the several forms of the present disclosure may be embodied in practice.

Claims

1-20. (canceled)

- 21. A method for fabricating a stacked staggered electrode capacitor, comprising the steps of: coating a conductive polymer cathode layer on to a planar anode sheet to form one or more capacitor core assemblies each defined by an assembly top surface corresponding to a cathode and an assembly bottom surface corresponding to an anode; forming one or more vertical insulator channels spaced apart along the one of the capacitor core assemblies; filling the vertical insulator channels with an insulator material; seed metallizing the assembly top surface and the assembly bottom surface to form a seeded cathode metal layer and a seeded anode metal layer; plating the seeded cathode metal layer and the seeded anode metal layer to form a cathode electrode plating and an anode electrode plating; and etching the cathode electrode plating and the anode electrode plating to respectively define a top opening and a bottom opening to the insulator material, the cathode electrode plating being staggered relative to the anode electrode plating with the top opening being laterally offset from the bottom opening.
- **22**. The method of claim 21, further comprising: laminating a plurality of the capacitor core assemblies with build-up layers separating one of the capacitor core assemblies from another to form a capacitor stack; routing one or more slots through the capacitor stack at least partially coextensively with the top and bottom openings defined by the cathode electrode plating and the anode electrode plating of respective ones of the capacitor core assemblies; and metal plating the one or more slots, a cathode connecting electrode being defined along a first side of one of the slots and electrically connected to the cathode electrode plating of at least one of the capacitor core assemblies, and an anode connecting electrode being defined along a second side of one of the slots and electrically connected to the anode electrode plating of at least one of the capacitor core assemblies.
- **23**. The method of claim 22, wherein laminating the plurality of capacitor core assemblies includes an application of a top build-up layer on an uppermost one of the capacitor core assemblies and a bottom build-up layer on a lowermost one of the capacitor core assemblies, the method further including metal plating at least a part of both the top build-up layer and the bottom build-up layer and electrically connect to the cathode connecting electrode and to the anode connecting electrode.
- **24**. The method of claim 22, wherein the cathode connecting electrode is connected to the cathode electrode plating of each of the capacitor core assemblies.
- **25**. The method of claim 24, further comprising: singulating a stacked capacitor unit from the capacitor stack.
- **26**. The method of claim 24, wherein the metal plating of the one or more slots and the part of the top build-up layer and the bottom build-up layer is with copper.
- **27**. The method of claim 24, wherein the insulator material is an epoxy material.
- **28**. The method of claim 22, further comprising: mounting the one or more capacitor core assemblies onto a frame.
- **29**. The method of claim 28, wherein the one or more vertical channels extend through the conductive cathode layer and the planar anode sheet to the frame.
- **30**. A method for fabricating a stacked staggered electrode capacitor, comprising the steps of: fabricating a plurality of capacitor core assemblies, each including a cathode electrode plating and an anode electrode plating; laminating a plurality of the capacitor core assemblies with build-up layers separating one of the capacitor core assemblies from another to form a capacitor stack; routing one or more slots through the capacitor stack at least partially coextensively with top and bottom openings defined by the cathode electrode plating and the anode electrode plating of respective ones of the capacitor core assemblies; and metal plating the one or more slots, a cathode connecting electrode being defined along a first side of one of the slots and electrically connected

to the cathode electrode plating of at least one of the capacitor core assemblies, and an anode connecting electrode being defined along a second side of one of the slots and electrically connected to the anode electrode plating of at least one of the capacitor core assemblies.

- **31**. The method of claim 30, wherein laminating the plurality of capacitor core assemblies includes an application of a top build-up layer on an uppermost one of the capacitor core assemblies and a bottom build-up layer on a lowermost one of the capacitor core assemblies, the method further including metal plating at least a part of both the top build-up layer and the bottom build-up layer and electrically connect to the cathode connecting electrode and to the anode connecting electrode.
- **32**. The method of claim 30, wherein the cathode connecting electrode is connected to the cathode electrode plating of each of the capacitor core assemblies.
- **33**. The method of claim 32, further comprising: singulating a stacked capacitor unit from the capacitor stack.
- **34**. The method of claim 32, wherein the metal plating of the one or more slots and the part of the top build-up layer and the bottom build-up layer is with copper.
- **35**. The method of claim 32, wherein the insulator material is an epoxy material.
- **36.** A method for fabricating a stacked staggered electrode capacitor, comprising the steps of: forming one or more capacitor core assemblies each defined by a cathode and an anode; forming one or more vertical insulator channels in one of the capacitor core assemblies filled with an insulator material; metal plating the cathode and the anode; etching the cathode and the anode to respectively define a first opening and a second opening to the insulator material, the cathode being staggered relative to the anode; laminating a plurality of the capacitor core assemblies with build-up layers separating one of the capacitor core assemblies from another to form a capacitor stack; routing one or more slots through the capacitor stack at least partially coextensively with first and second openings of each of the one or more capacitor core assemblies; and metal plating the one or more slots.
- **37**. The method of claim 36, further comprising: seed metalizing the cathode and the anode prior to metal plating.
- **38**. The method of claim 36, wherein the first opening is laterally offset from the second opening.
- **39**. The method of claim 36, wherein laminating the plurality of capacitor core assemblies includes an application of a top build-up layer on an uppermost one of the capacitor core assemblies and a bottom build-up layer on a lowermost one of the capacitor core assemblies, the method further including metal plating at least a part of both the top build-up layer and the bottom build-up layer and electrically connect to the cathode connecting electrode and to the anode connecting electrode.
- **40**. The method of claim 36, wherein the cathode connecting electrode is connected to the cathode of each of the capacitor core assemblies.